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		APJ ABDUL KALAM TECHNOLOGICAL UNIVERSITY FIRST SEMESTER B.TECH DEGREE EXAMINATION, APRIL 2018	•
		Course Code: BE101-04	
		Course Name: INTRODUCTION TO ELECTRONICS ENGINEERING	
Ma	x. Mai	ks: 100 · Duration: 3	Hours
		PART A	
		Answer all questions, each carries 5 marks.	Marks
1		With a neat diagram, explain the constructional features of an electrolytic capacitor.	(5)
2	a)	Explain how a varactor diode can be used in tuned circuits?	(3)
	b)	Explain the term peak inverse voltage (PIV) of a diode.	(2)
3		Draw the output V-I characteristicsofa common emitter amplifier and mark	(5)
		theoperating point on the load line for $V_{CE} = 6V$ and base current $I_b = 0.2mA$, take β as 50.	
4		Give the structure of an enhancement typeMOSFET and why it is called so.	(5)
5		Draw the voltage transfer characteristics of a general limiter circuit and explain how it act as clipper.	(5)
6		Draw the circuit diagramof a voltage doubler and explain the working.	(5)
7		Define the terms accuracy and precision of a measuring device?	(5)
8		How do you test an NPN as well as a PNP transistor using multimeter?	(5)
		PART B	
		Answer six questions, one full question from each module and carries 10 marks.	
9	۵)	Module I	(4)
9	a) b)	What are the advantage of carbon film resistor over carbon composition resistors. Give the constructional features of carbon film resistor with a neat diagram.	(4) (6)
	0)	OR	(0)
10	a)	How cooling is effected in high power wire wound resistors.	(4)
	b)	Explain the constructional features of a wire wound resistor with a diagram.	(6)
		Module II	
П	a)	Draw the V-I characteristics of a Silicon diode. The above diode is forward biased	(5)
		with a dc supply voltage of 5 V. Find the Q points for 1.1 k Ω and 2.2 k Ω of load	
	b)	resistance. (Assume cut in voltage of diode is 0.6 v).	(5)
	b)	With the help of a diagram, explain the working of a photo diode. OR	(5)
12	a)	What is drift current and diffusion current in a semiconductor?	(5)
	b)	How the barrier potential is developed across a PN Junction?	(5)
	-	Module III	
13	a)	Distinguish between common emitter and common base current gain of a transistor and derive a relation between them.	(5)
	b)	Explain the biasing condition applied across different junctions of a transistor in active, saturation and cut-off regions.	(5)

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		OR	
14	a)	Draw and explain the circuit of a common emitter RC coupled amplifier using NPN transistorwith voltage divider biasing.	(6)
	b)	Draw the frequency response of a RC coupled amplifier and explain how gain reduces at low and high frequencies.	•(4)
		Module IV	
15	a)	Draw the V _{DS} v/s I _D curve of an enhancement MOSFET and mark different operating regions.	(3)
	b)	With help of neat sketches, explain how an increase in V _{DS} affects channel field and drain current in a MOSFET.	(7)
		OR	
16	a)	Draw the structure of N channel depletion MOSFET.	(3)
	b)	Explain the working of a depletion mode MOSFET.	(7)
		Module V	
17	a)	Draw the circuit of a full wave bridge rectifier and derive the equations for V_{rms} , V_{dc} and ripple factor.	(7)
	b)	Explain the term rectifier efficiency. http://www.ktuonline.com OR	(3)
18	a)	Draw the block diagram of a DC power supply and explain the working of each stage.	(5)
	b)	Find the minimum and maximum current flowing through the Zener diodeas shown in figure for a regulated output of 5 V. Choose proper value for R _L .	(5)
		7-8 V	
		Module VI	
19	a)	Draw the block diagram and explain the working of a CRO.	(6)
	b)	Explain with help of diagrams, how phase difference between two signals can be measured using CRO.	(4)
		OR	
20	a)	Draw the block diagram and explain the working of a digital storage oscilloscope.	(6)
	b)	List and describe the various types of measurement errors.	(4)

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